a. •	· ·		HOV O 1 DO	ان در			SHEE	ET 1 OF
Form PTC			U.S. OGRARTMEN		ATTY DOCKET NO.		SERIAL N	10.
Modified				ADEMARK OFFICE	210136US99	!	09/901,1	109
					APPLICANT			
LIS	ST OF	REFEF	RENCES CITED BY A	PPLICANT	Ravindranath DROOPAD et a	al		
					FILING DATE		GROUP	
					July 10, 2001	- 	2815	
			*		U.S. PATENT DOCUMENTS			
EXAM! INITI			DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATI
W	Wh.	zv	5,122,679	06/16/92	ISHII ET AL			
7	.7	zw	6,232,806	05/15/01	WOESTE ET AL			
		ZX	5,430,397	07/04/95	ITOH ET AL			
	<u> </u>	ZY	6,151,240	11/21/00	SUZUKI	T		
·		ZZ	6,528,374	03/04/03	BOJARCZUK, JR ET AL			
		A1	6,589,887	07/08/03	DALTON ET AL			
	1	A2	5,064,781	11/12/91	CAMBOU ET AL			
	\top	А3	2002/0052061	05/02/02	FITZGERALD			
	1	A4	5,696,392	12/09/97	CHAR ET AL			
	1/	A5	5,986,301	11/16/99	FUKUSHIMA ET AL			
<u></u>	√	A6	6,329,277	12/11/01	LIU ET AL			
	~	A7						
	_	A8			·			
		A9		· .				
				FC	OREIGN PATENT DOCUMENTS			
	- 4		DOCUMENT NUMBER	DATE	COUNTRY		YES	TRANSLATION NO
M	M	ccs	WO 99/67882	12/29/99	WIPO			
* / -	Z	ССТ	WO 95/02904	01/26/95	WIPO			
	7_	CCU	WO 02/009150	01/31/02	WIPO			
		ccv	0 766 292	04/02/97	EUROPE			
		ccw	198 29 609	01/05/00	GERMANY			
		ссх	1 069 605	01/17/01	EUROPE			
		CCY	0 828 287	03/11/98	EUROPE			
		ccz	1 176 230	01/30/02	EUROPE			
	T		OTHER F	REFERENCES	(Including Author, Title, Date, Pertine	ent Pages, e	tc.)	
	+-	Γ	Yi W. et al; "Mechan	ism of cleaning	Si (100) surface using Sr and SrO for the	he growth of	crystalline !	SrTiO/sub 2/films" Jo
		LLAP	of Vacuum Science 8	& Technology, V	Vol. 20, No. 4, July 2002 (2002-07) pp. 1	1402-1405		
	\bigvee	LLAQ			formation for the epitaxial growth of SrTi 51-266	O/sub 3/on a	illicon" Mate	erials Research Sou
		LLAR						
		LLAS	1 Tarta	7	>-	Add	itional Refe	erences sheet(s) atta
		1 / 2	17 10 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	· / · · · ·				12